

Is Now Part of



ON Semiconductor®

To learn more about ON Semiconductor, please visit our website at
www.onsemi.com

Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

March 2016

FDMA410NZT

Ultra Thin N-Channel 1.5 V PowerTrench® MOSFET

20 V, 9.5 A, 23 mΩ

Features

- 0.55mm max package height MicroFET 2x2mm Package
- Max $r_{DS(on)}$ = 23 mΩ at V_{GS} = 4.5 V, I_D = 9.5 A
- Max $r_{DS(on)}$ = 29 mΩ at V_{GS} = 2.5 V, I_D = 8.0 A
- Max $r_{DS(on)}$ = 36 mΩ at V_{GS} = 1.8 V, I_D = 4.0 A
- Max $r_{DS(on)}$ = 60 mΩ at V_{GS} = 1.5 V, I_D = 2.0 A
- HBM ESD protection level > 1.5 kV (Note 3)
- RoHS Compliant

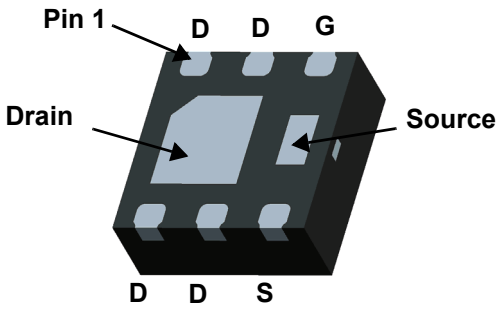
General Description

This Single N-Channel MOSFET has been designed using Fairchild Semiconductor's advanced Power Trench process to optimize the $r_{DS(ON)}$ @ V_{GS} = 1.5 V on special MicroFET leadframe.

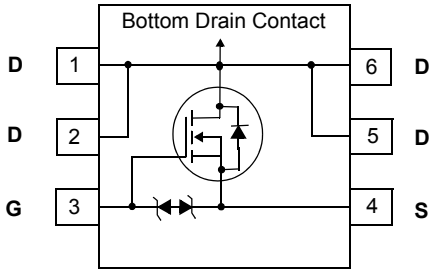
This design is similar to the FDMA410NZ, however it features our new advanced 0.55mm max 2x2 MLP package technology.

Applications

- Li-Ion Battery Pack
- Baseband Switch
- Load Switch
- DC-DC Conversion
- Mobile Device Switching



MicroFET 2X2 (Bottom View)



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V_{DS}	Drain to Source Voltage			20	V
V_{GS}	Gate to Source Voltage			±8	V
I_D	-Continuous	T_A = 25 °C	(Note 1a)	9.5	A
	-Pulsed		(Note 4)	63	
P_D	Power Dissipation	T_A = 25 °C	(Note 1a)	2.4	W
	Power Dissipation	T_A = 25 °C	(Note 1b)	0.9	
T_J, T_{STG}	Operating and Storage Junction Temperature Range			-55 to +150	°C

Thermal Characteristics

$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1a)	52	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	(Note 1b)	145	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
410T	FDMA410NZT	MicroFET 2X2	7 ”	8 mm	3000 units

©2016 Fairchild Semiconductor Corporation

Electrical Characteristics T_J = 25 °C unless otherwise noted

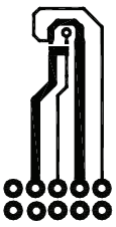
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		15		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 16 V, V_{GS} = 0 V			1	μA
I_{GSS}	Gate to Source Leakage Current	V_{GS} = ±8 V, V_{DS} = 0 V			±10	μA
On Characteristics						
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	0.4	0.8	1.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		–3		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 4.5 V, I_D = 9.5 A		14	23	mΩ
		V_{GS} = 2.5 V, I_D = 8.0 A		18	29	
		V_{GS} = 1.8 V, I_D = 4.0 A		25	36	
		V_{GS} = 1.5 V, I_D = 2.0 A		35	60	
		V_{GS} = 4.5 V, I_D = 9.5 A, T_J = 125 °C		21	32	
g_{FS}	Forward Transconductance	V_{DD} = 5 V, I_D = 9.5 A		36		S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz		935	1310	pF
C_{oss}	Output Capacitance			122	170	pF
C_{rss}	Reverse Transfer Capacitance			84	118	pF
R_g	Gate Resistance	f = 1 MHz	0.1	1.4	3.0	Ω
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 10 V, I_D = 9.5 A, V_{GS} = 4.5 V, R_{GEN} = 6 Ω		8.5	17	ns
t_r	Rise Time			3.0	10	ns
$t_{d(off)}$	Turn-Off Delay Time			27	44	ns
t_f	Fall Time			3.3	10	ns
Q_g	Total Gate Charge	V_{GS} = 4.5 V , V_{DD} = 10 V, I_D = 9.5 A		10	14	nC
Q_{gs}	Gate to Source Charge			1.2		nC
Q_{gd}	Gate to Drain “Miller” Charge			2.0		nC
Drain-Source Diode Characteristics						
I_S	Maximum Continuous Drain-Source Diode Forward Current				2.0	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 2.0 A (Note 2)		0.7	1.2	V
t_{rr}	Reverse Recovery Time	I_F = 9.5 A, di/dt = 100 A/μs		16	30	ns
Q_{rr}	Reverse Recovery Charge			4.5	10	nC

NOTES:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JA}$ is determined by the user's board design.



a.52 °C/W when mounted on a 1 in^2 pad of 2 oz copper.



b. 145 °C/W when mounted on a minimum pad of 2 oz copper.

2. Pulse Test: Pulse Width < 300 ms, Duty cycle < 2.0%.
3. The diode connected between the gate and source serves only as protection against ESD. No gate overvoltage rating is implied.
4. Pulsed Id please refer to Fig.11 SOA curve for more details.

Typical Characteristics T_J = 25 °C unless otherwise noted

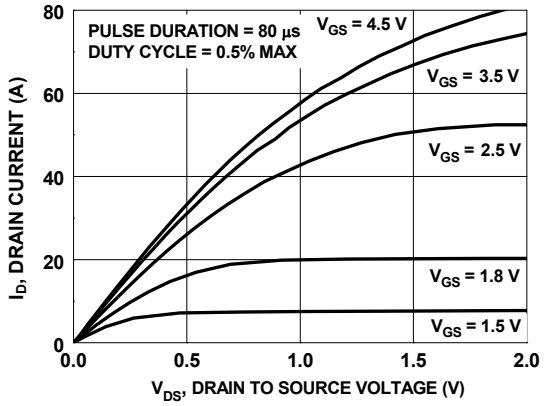


Figure 1. On Region Characteristics

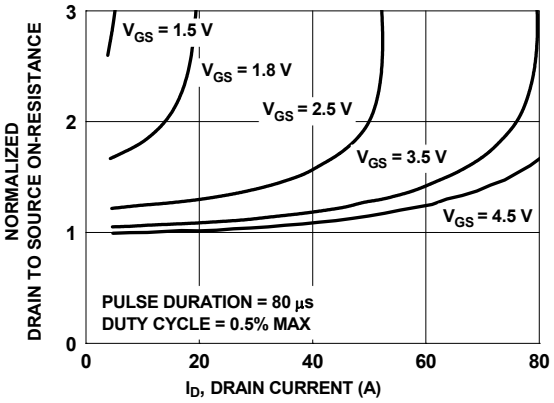


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

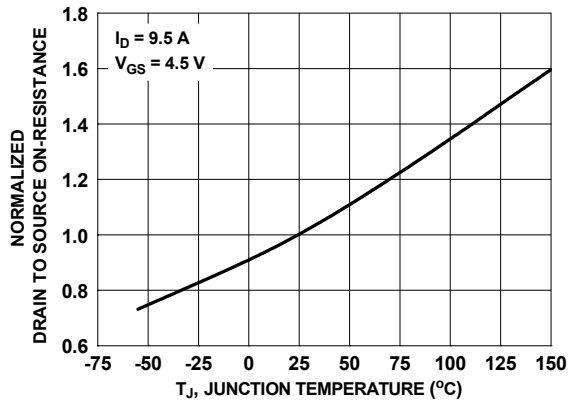


Figure 3. Normalized On Resistance vs Junction Temperature

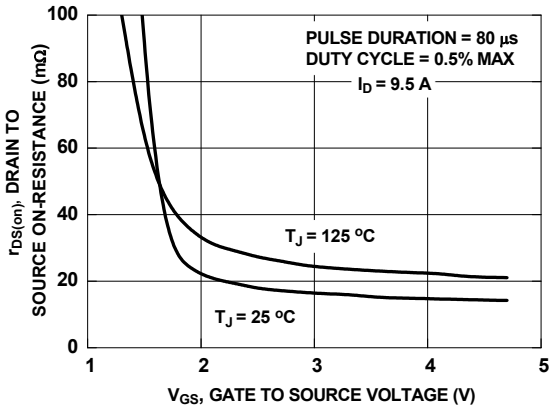


Figure 4. On-Resistance vs Gate to Source Voltage

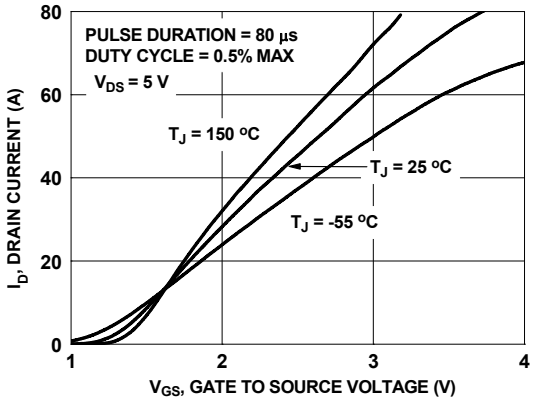


Figure 5. Transfer Characteristics

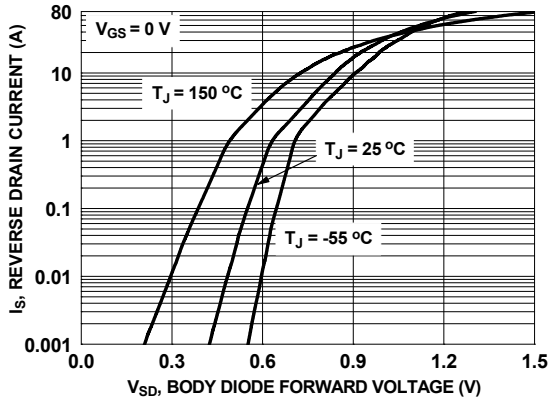


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

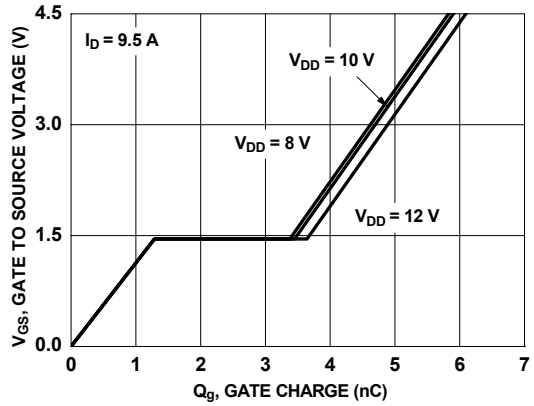


Figure 7. Gate Charge Characteristics

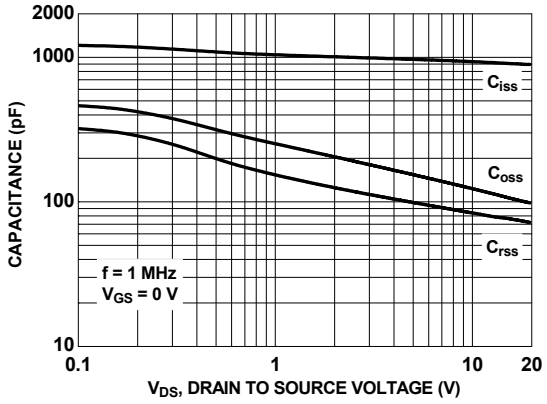


Figure 8. Capacitance vs Drain to Source Voltage

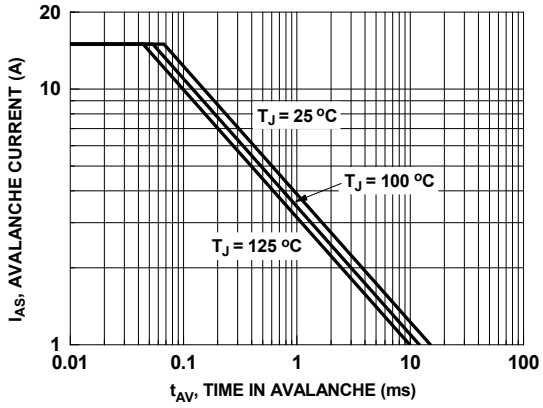


Figure 9. Unclamped Inductive Switching Capability

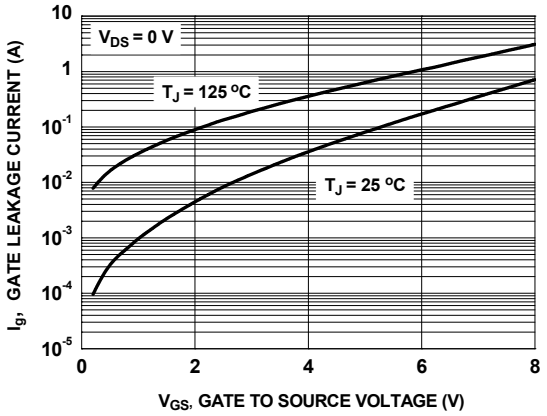


Figure 10. Gate Leakage Current vs Gate to Source Voltage

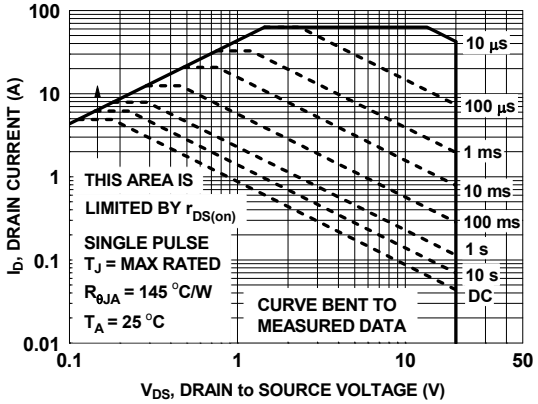


Figure 11. Forward Bias Safe Operating Area

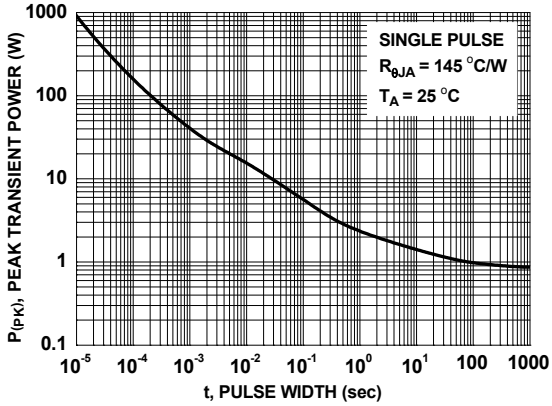


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

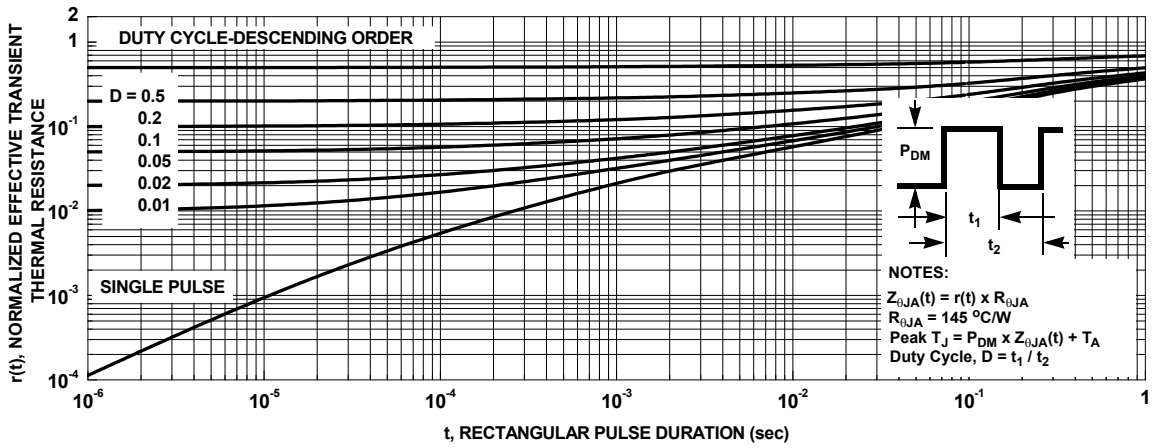
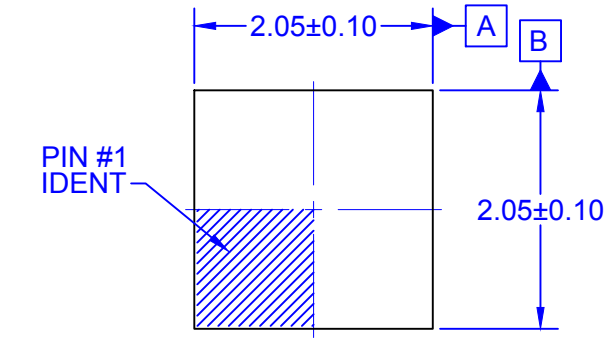
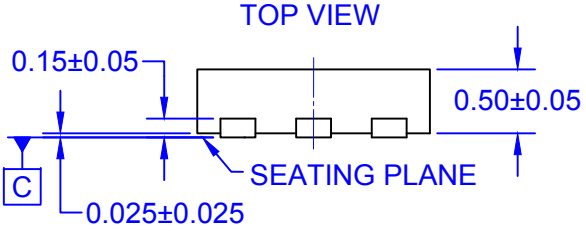


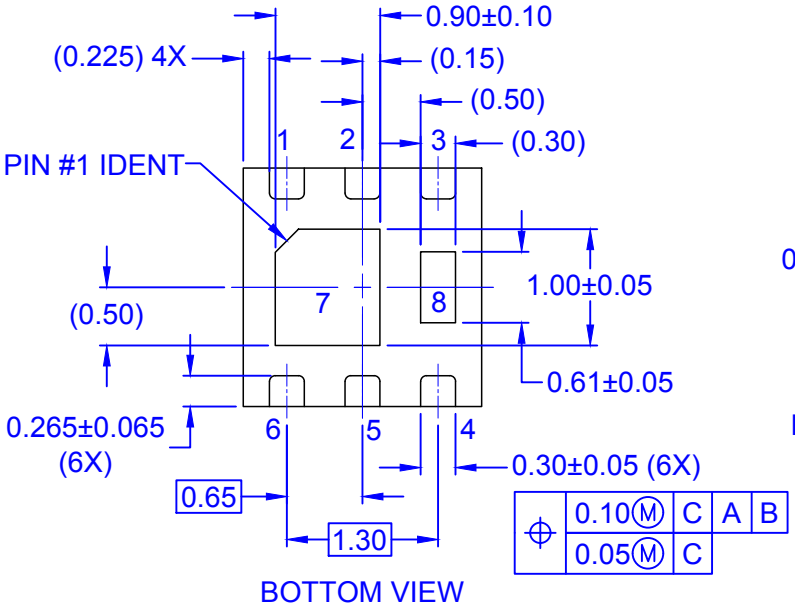
Figure 13. Junction-to-Case Transient Thermal Response Curve



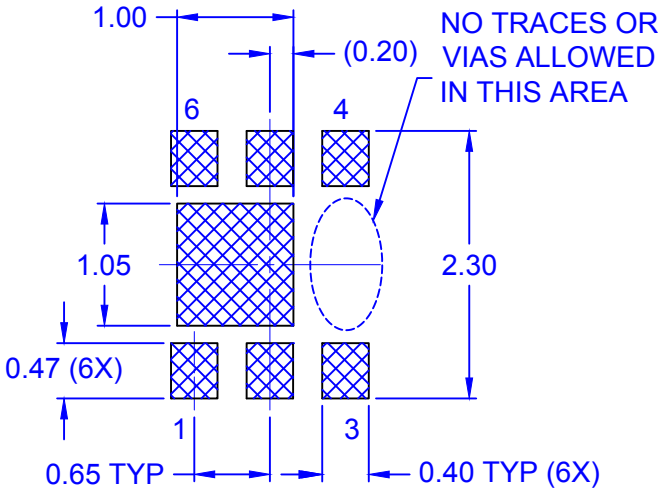
TOP VIEW



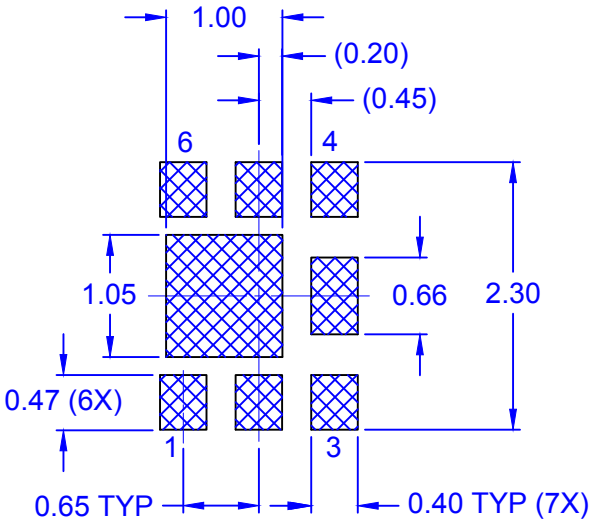
SIDE VIEW



BOTTOM VIEW



RECOMMENDED LAND PATTERN OPT 1



RECOMMENDED LAND PATTERN OPT 2

ON Semiconductor

NOTES:

A. PACKAGE DOES NOT CONFORM TO ANY JEDEC STANDARD.
B. DIMENSIONS ARE IN MILLIMETERS.
C. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
D. DRAWING FILENAME: MKT-FR015L3TrevB.

ON Semiconductor and ON are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

Unikeyic Electronics

Global Electronic Components Distributor

Click to view pricing, inventory, delivery, and lifecycle information:

ON Semiconductor:

SVC704-TL-E MC14538BDTR2G 1N5344BRLG FAN3229TMX-F085 FDMS86202 FOD3120SDV
NTS2101PT1G MVMBF0201NLT1G NL17SZ126DFT2G SBAT54CWT1G-M02 1N4749ATR FDMC86261P
MMSZ5255BT1G QT7810X 74ABT541CMTC CAT823TTDI-GT3 ESD9X7.0ST5G MC34161DG
NCV20072DR2G NTS4101PT1G RB751V40T1G 74LCX244WM CAV25M01YE-GT3 BAS19LT3G
MC74LVX244DWR2G MC7815CTG NCV431BSNT1G NCV7344AD10R2G LM2901MX MMVL2101T1G